

PHENITEC

SEMICONDUCTOR

RCP6V4x

Transient Voltage Suppressor

Features

- ANODE-Common Structure (Dual TVS)
- Suitable to small packages(SOT-363) Chip Size=0.40mmsq
- High ESD protection level
IEC61000-4-2(ESD) +/-30kV(Air) +/-30kV(Contact)

Applications

It is intended for use in voltage and ESD sensitive equipment such as:

- Computers
- Printers
- Communication systems

Item	Characteristics
Wafer Size	5inch
Chip Size	400*400um

Maximum Ratings (Ta=25degC)

Symbol	Parameter	Value	Units
Ppk	Peak Power Dissipation @=8/20us (*1)	80.5	W
Ipp	Maximum Peak Pulse Current @=8/20us (*1)	7.0	A
Pd	Power Dissipation	350	mW
Tj	Maximum Junction Temperature (*1)	150	degC
Tstg	Storage Temperature Range	-55 to+150	degC
Vpp	Electrostatic Discharge		
	IEC61000-4-2 Air Discharge (*1)	±30	kV
	IEC61000-4-2 Contact Discharge (*1)	±30	kV

(*1) Rating value for reference on a SOT-23 package configuration (front: Au wire 35um, back: Au eutectic), mounted on PCB of 1.5cm by 2.5cm.

Electrical Characteristics (Ta=25degC)

Parameter	Symbol	Min	Typ.	Max	Unit	Condition
Breakdown Voltage	VBR	6.4	6.8	7.2	V	IR=5mA
Leakage Current	IRM	-	-	1.0	uA	Vrwm=5V
Forward Voltage Drop	VF	-	-	1.25	V	IF=10mA
Typical Capacitance	C	-	40	-	pF	0V , 1MHz
Dynamic Impedance	ZzT	-	-	30	ohm	Iz=5mA
Knee Dynamic Impedance	ZzK	-	-	300	ohm	Iz=0.5mA
Clamping Voltage	Vc			11.5	V	Ipp=7.0A *1

*1 Package=SOT-23 (front: Au wire 35um, back: Au eutectic),